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Application No. <u>09/883,795</u>	Prepared by <u>BSH</u>	Tracking Number <u>05932246</u>	
Examiner-GAU <u>CAO-2814</u>	Date <u>05/13/2004</u>	Week Date <u>04-12-2004</u>	
	No. of queries <u>1</u>	IPW RU4	

JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION	MESSAGE
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Form 1449\*

Atty. Docket No.: 303.355US4

Serial No. Unknown

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TD	4,113,515	09/12/1978	Kooi, E., et al.	148	1.5	03/29/76
TD	4,460,670	07/01/1984	Ogawa, et al.	430	57	11/19/82
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TD	5,145,741	09/01/1992	Quick	428	402	02/28/91
TD	5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
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TD	5,449,941	09/12/1995	Yamazaki, S., et al.	257	411	10/27/92
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TD	5,622,112	04/22/1997	Yamazaki, S., et al.	438	259	04/28/95
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TD	5,654,208	08/05/1997	Harris, C., et al.	438	522	05/08/95

Examiner

Theresa J. Brown

Date Considered

12/14/01

\*Substitute Disclosure Statement Form PTO-1449.

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Form 1449\*

Atty. Docket No.: 303.355US4

Serial No. Unknown 09/883,795INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

Applicant: Leonard Forbes et al.

09/883,795

(Use several sheets if necessary)

Filing Date: Herewith

Group: Unknown 254

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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TD	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
TD	01-115162	05/08/1989	Japan	H01L	29/78	
TD	0291951	08/04/1993	European	H01L	29/64	
TD	03-222367	10/01/1991	Japan	H01L	29/784	
TD	04-056769	02/24/1992	Japan	C23C	16/32	
TD	06-224431	08/12/1994	Japan	H01L	29/784	
TD	06-302828	10/28/1994	Japan	H01L	29/788	
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TD	07-115191	05/02/1995	Japan	H01L	29/78	
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Examiner

*Thompson*

Date Considered

12/04/01

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\*\*EXAMINER Initial of vital importance: whether or not citation is in accordance with MPEP 2144. Also the initial of the examiner who made the citation. Include a "1" in the box with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al. 9/885 745	
	Filing Date: Herewith	Group: Unknown

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Invention Number No	Date	Country	Class	Subclass	Translation
						Yes
70	63-181473	07/26/1988	Japan	HO1L	29/78	
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Examiner <u>Theresa Brown</u>	Date Considered <u>12/12/96</u>
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\*Substitute Disclosure Statement Form PTO 1449

\*\*EXAMINER: Initial if citation considered whether or not citation is in compliance with MPEP 2112. Draw line through citation if not in compliance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al. <span style="float: right;">89/355745</span>	
	Filing Date: Herewith	Group: Unknown

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\*\*Examiner  
Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

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Date Considered

\*Substitute Disclosure Statement Form PTO 1449\*

\*\*EXAMINER: Initial if citation considered whether or not citation is in accordance with MPEP 2.107. If not in accordance and not considered, include copy of this form with next communication to applicant.

Form 1449\*

Atty. Docket No.: 303.355US4

Serial No. Unknown

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

## OTHER DOCUMENTS

\*\*Examiner  
Initial

Including Author, Title, Date, Pertinent Pages, Etc.

10	Maury, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", <u>Surface and Coatings Technology</u> , 76-77, 119-125, (1995)
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Examiner

Date Considered

\*Substitute Disclosure Statement Form 1449-1449.

\*\*EXAMINER: Initial if citation considered; otherwise, do not. If citation is in accordance with MPEP 21.11, draw line and mark "not in accordance" and not considered. Include copy of this form with next communication to applicant.